

3DD103, 3DD104**NPN Silicon Low Frequency High Power Transistor****Features:**

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97 for all, QZJ840611A, QZJ840611 for 3DD103.
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP for all, JT, JCT, GS, G, G+ for 3DD103.

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications				
			3DD103			3DD104	
			A	B	C	D	E
Collector-Emitter Voltage	V_{CEO}	V	200	300	400	600	800
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	200	300	400	600	800
Emitter-Base Voltage	V_{EBO}	V	4			A~C: 4, D~E: 8	
Max. Collector Current	I_{CM}	A	3				
Max. Collector Dissipation	P_{CM}	W	50 ($T_c \leq 75^\circ\text{C}$)				
Junction Temperature	T_{jm}	$^\circ\text{C}$	175				
Storage Temperature	T_{stg}	$^\circ\text{C}$	-55~+175				
Collector-Emitter Leakage Current	I_{CEO}	mA	1.0 ($V_{CE}=100\text{V}$)				
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	A~B: 2.0, C~E: 4.0 ($I_C=3\text{A}, I_B=1\text{A}$)				
DC Current Gain	h_{FE}		Min.:10 ($V_{CE}=10\text{V}, I_C=1.5\text{A}$)				
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	A~C: ≥ 5 , D~E: 8 ($I_E=5\text{mA}$)				

Outline and Dimensions: